

N-channel 100 V, 65 mΩ standard level MOSFET in LFPAK56 8 May 2013 Product data sheet

1. General description

Standard level N-channel MOSFET in an LFPAK56 (Power SO8) package using TrenchMOS technology. This product has been designed and qualified to AEC Q101 standard for use in high performance automotive applications.

2. Features and benefits

- Q101 compliant
- Repetitive avalanche rated
- Suitable for thermally demanding environments due to 175 °C rating
- True standard level gate with V_{GS(th)} rating of greater than 1 V at 175 °C

3. Applications

- 12 V, 24 V and 48 V Automotive systems
- Motors, lamps and solenoid control
- Transmission control
- Ultra high performance power switching

4. Quick reference data

Table 1. Qui	ck reference data					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C	-	-	100	V
I _D	drain current	V _{GS} = 10 V; T _{mb} = 25 °C; <u>Fig. 1</u>	-	-	19	А
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 2</u>	-	-	64	W
Static charact	eristics	·	1			
R _{DSon}	drain-source on-state resistance	V _{GS} = 10 V; I _D = 5 A; T _j = 25 °C; <u>Fig. 11</u>	-	44	65	mΩ
Dynamic char	acteristics					
Q _{GD}	gate-drain charge	V _{GS} = 10 V; I _D = 5 A; V _{DS} = 80 V; T _j = 25 °C; <u>Fig. 13</u> ; <u>Fig. 14</u>	-	7	-	nC

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5. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source	mb	D
2	S	source		
3	S	source	q	G-UFT4
4	G	gate	មុប្បូប្	mbb076 S
mb	D	mounting base; connected to drain	1 2 3 4 LFPAK56; Power- SO8 (SOT669)	

6. Ordering information

Table 3. Ordering information							
Type number	Package						
	Name	Description	Version				
BUK7Y65-100E	LFPAK56; Power-SO8	Plastic single-ended surface-mounted package (LFPAK56; Power-SO8); 4 leads	SOT669				

7. Marking

Table 4. Marking codes	
Type number	Marking code
BUK7Y65-100E	76510E

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

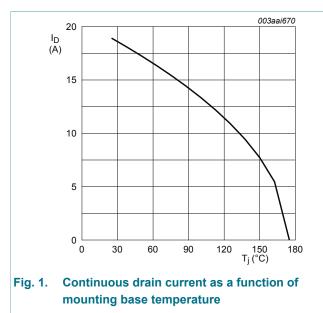
Symbol	Parameter	Conditions	Min	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C	-	100	V
V _{DGR}	drain-gate voltage	R _{GS} = 20 kΩ	-	100	V
V _{GS}	gate-source voltage	T _j ≤ 175 °C; DC	-20	20	V
I _D	drain current	T _{mb} = 25 °C; V _{GS} = 10 V; <u>Fig. 1</u>	-	19	А
		T _{mb} = 100 °C; V _{GS} = 10 V; <u>Fig. 1</u>	-	13.4	А
I _{DM}	peak drain current	T_{mb} = 25 °C; pulsed; $t_p \le 10 \ \mu s$; Fig. 4	-	76	А
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 2</u>	-	64	W
T _{stg}	storage temperature		-55	175	°C

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Symbol	Parameter	Conditions		Min	Max	Unit
Tj	junction temperature			-55	175	°C
Source-drai	in diode					
l _S	source current	T _{mb} = 25 °C		-	19	А
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$		-	76	А
Avalanche i	ruggedness					
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	$\label{eq:ID} \begin{array}{l} I_{D} = 19 \; A; \; V_{sup} \leq 100 \; V; \; R_{GS} = 50 \; \Omega; \\ V_{GS} = 10 \; V; \; T_{j(init)} = 25 \; ^{\circ}C; \; unclamped; \\ \hline Fig. \; 3 \end{array}$	[1][2]	-	25.3	mJ

[1] Single-pulse avalanche rating limited by maximum junction temperature of 175 $^\circ\text{C}.$

[2] Refer to application note AN10273 for further information.



 $V_{GS} \ge 10V$

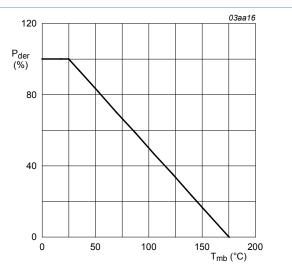
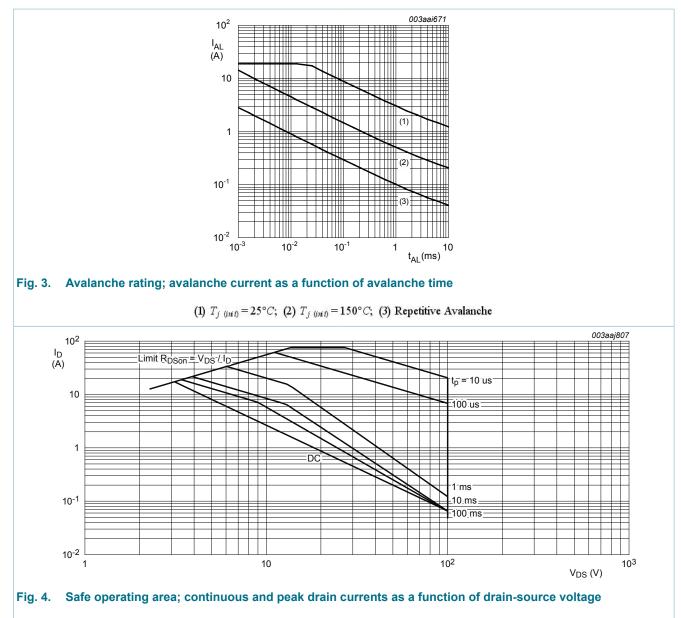


Fig. 2. Normalized total power dissipation as a function of mounting base temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \%$$

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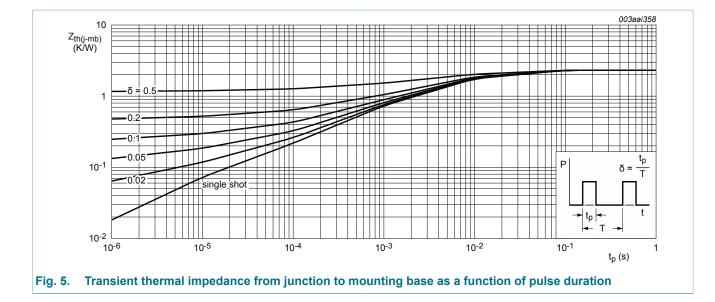


 $T_{mb} = 25^{\circ}C; \ I_{DM}$ is a single pulse

9. Thermal characteristics

Table 6. The	rmal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	<u>Fig. 5</u>	-	-	2.31	K/W

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10. Characteristics

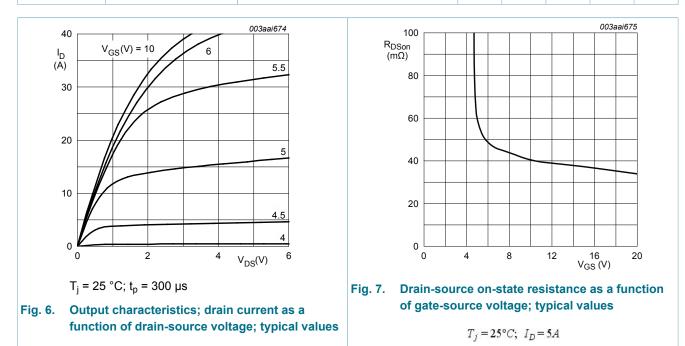
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					
breakdown	drain-source	I_D = 250 µA; V_{GS} = 0 V; T_j = 25 °C	100	-	-	V
	breakdown voltage	I _D = 250 μA; V _{GS} = 0 V; T _j = -55 °C	90	-	-	V
V _{GS(th)}	ss(th) gate-source threshold voltage	I_D = 1 mA; V_{DS} = V_{GS} ; T_j = 25 °C; Fig. 9; Fig. 10	2.4	3	4	V
		I_D = 1 mA; V_{DS} = V_{GS} ; T_j = -55 °C; Fig. 9	-	-	4.5	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ °C};$ Fig. 9	1	-	-	V
DSS drain leakage current	V_{DS} = 100 V; V_{GS} = 0 V; T_j = 25 °C	-	0.03	1	μA	
		V_{DS} = 100 V; V_{GS} = 0 V; T_j = 175 °C	-	-	500	μA
I _{GSS}	gate leakage current	V_{GS} = 20 V; V_{DS} = 0 V; T_j = 25 °C	-	2	100	nA
		V_{GS} = -20 V; V_{DS} = 0 V; T_j = 25 °C	-	2	100	nA
R _{DSon}	drain-source on-state	V _{GS} = 10 V; I _D = 5 A; T _j = 25 °C; <u>Fig. 11</u>	-	44	65	mΩ
	resistance	V _{GS} = 10 V; I _D = 5 A; T _j = 175 °C; Fig. 11; Fig. 12	-	-	180	mΩ
Dynamic ch	aracteristics					
Q _{G(tot)}	total gate charge	I _D = 5 A; V _{DS} = 80 V; V _{GS} = 10 V;	-	17.8	-	nC
Q _{GS} gate-source charge	gate-source charge	T _j = 25 °C; <u>Fig. 13; Fig. 14</u>	-	3.4	-	nC
Q _{GD}	gate-drain charge		-	7	-	nC

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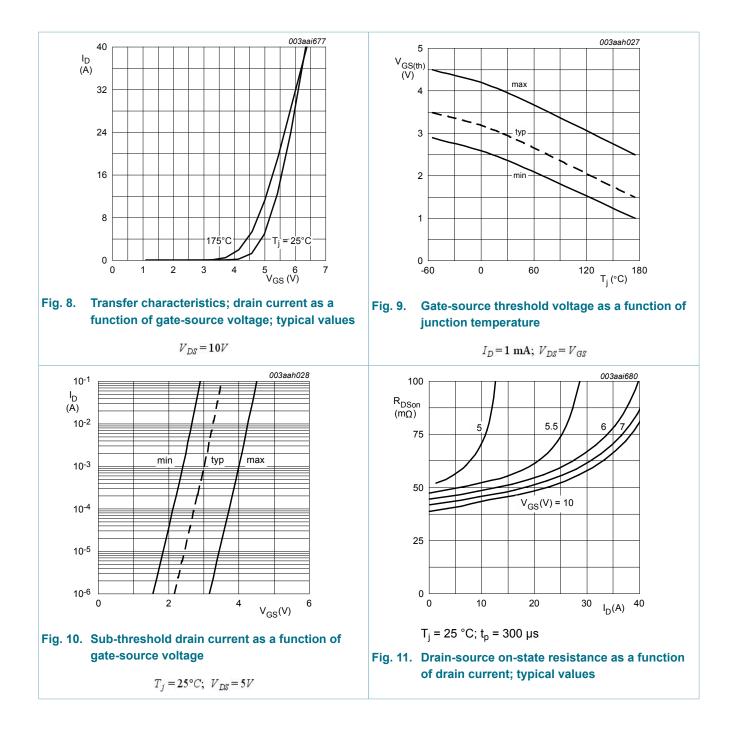
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Symbol	Parameter	Conditions		Min	Тур	Max	Unit
C _{iss}	input capacitance	V_{GS} = 0 V; V_{DS} = 25 V; f = 1 MHz;		-	768	1023	pF
C _{oss}	output capacitance	T _j = 25 °C; <u>Fig. 15</u>		-	99.5	119.4	pF
C _{rss}	reverse transfer capacitance			-	74.2	101.7	pF
t _{d(on)}	turn-on delay time	V_{DS} = 80 V; R _L = 10 Ω; V _{GS} = 10 V;		-	5.3	-	ns
t _r	rise time	R _{G(ext)} = 5 Ω; T _j = 25 °C		-	7.5	-	ns
t _{d(off)}	turn-off delay time			-	12.4	-	ns
t _f	fall time			-	8	-	ns
Source-dra	iin diode	1	1				
V_{SD}	source-drain voltage	I_{S} = 5 A; V_{GS} = 0 V; T_{j} = 25 °C; <u>Fig. 16</u>		-	0.82	1.2	V
t _{rr}	reverse recovery time	$I_{S} = 5 \text{ A}; \text{ d}I_{S}/\text{d}t = -100 \text{ A}/\mu\text{s}; \text{ V}_{GS} = 0 \text{ V};$		-	31.5	-	ns
Q _r	recovered charge	V _{DS} = 25 V; T _j = 25 °C		-	40.6	-	nC



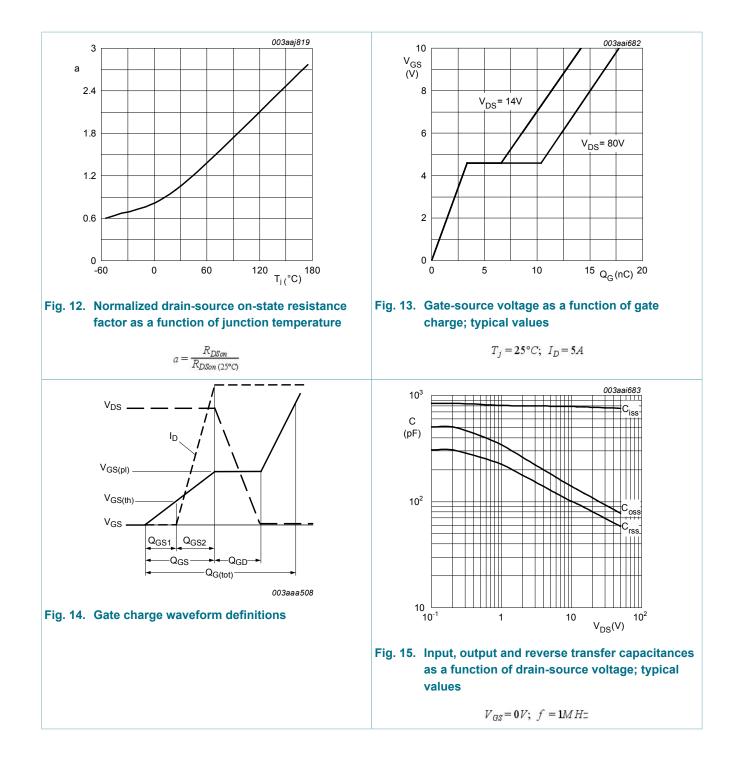
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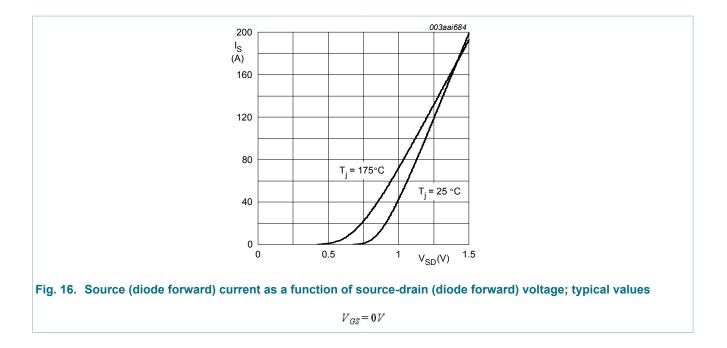
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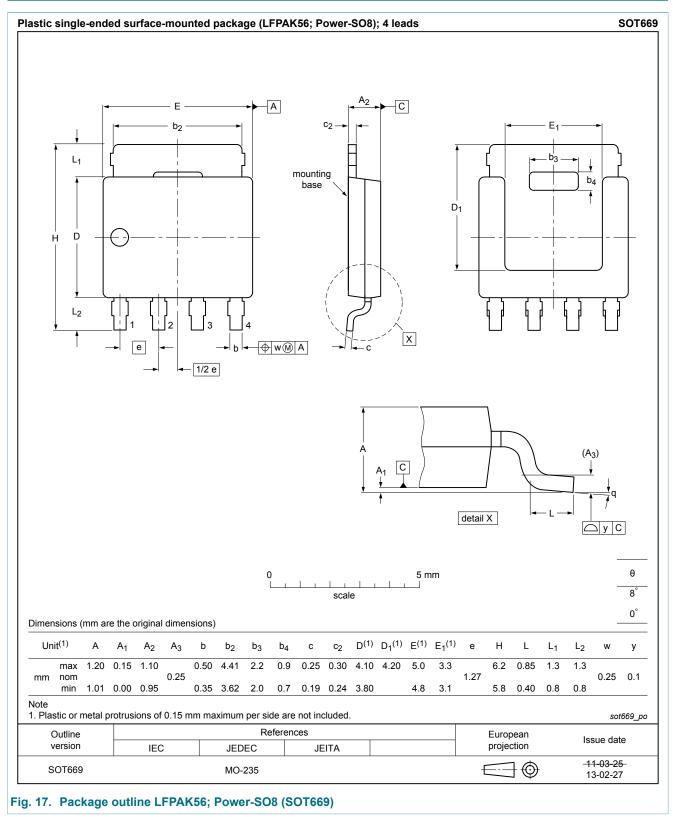
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11. Package outline



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12. Legal information

12.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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